



#### GPSF02M30EH Schottky Barrier Diode

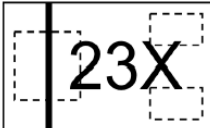
##### Feature

- Small surface mounting type
- Low reverse current and low forward voltage
- High reliability

##### Application

- High speed switch for detection
- For portable equipment:( Mobile phone, MD, Note book PC, etc.)

##### MARKING:



23 = Device Code  
X = Date Code

##### DFN1006-3L



Schematic diagram



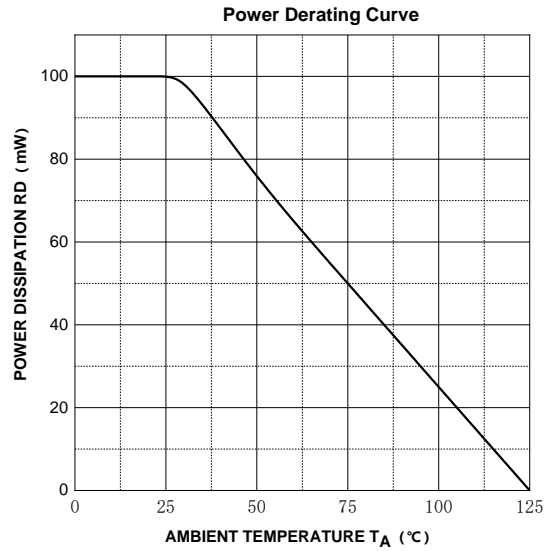
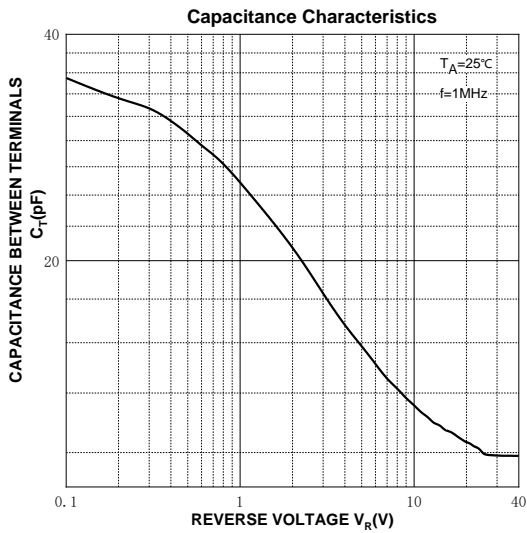
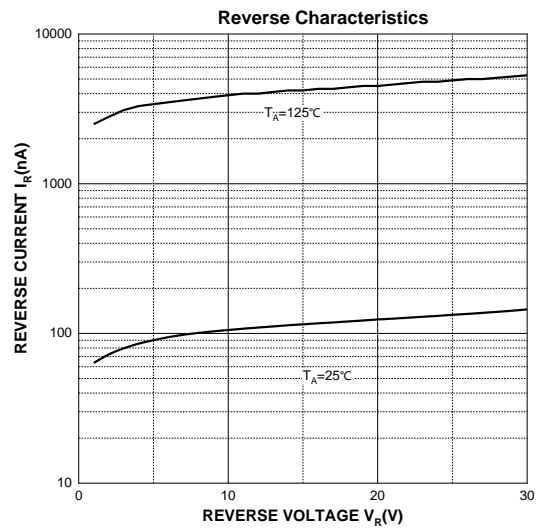
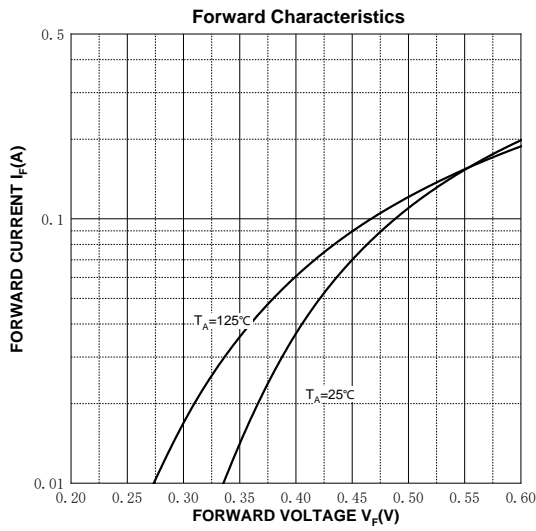
#### ABSOLUTE MAXIMUM RATINGS (T<sub>A</sub>=25°C unless otherwise noted)

Parameter	Symbol	Value	Unit
DC Reverse Voltage	V <sub>R</sub>	30	V
RMS Reverse Voltage	V <sub>R(RMS)</sub>	21	V
Mean Rectifying Current	I <sub>O</sub>	0.1	A
Non-repetitive Peak Forward Surge Current @ t=8.3ms	I <sub>FSM</sub>	0.5	A
Power Dissipation	P <sub>D</sub>	100	mW
Thermal Resistance From Junction To Ambient	R <sub>θJA</sub>	1000	°C/W
Junction Temperature	T <sub>J</sub>	125	°C
Storage Temperature	T <sub>STG</sub>	-55 ~ +150	°C

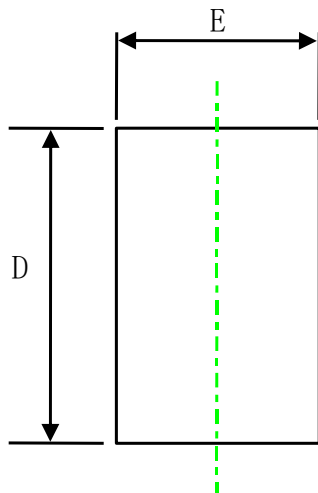
#### ELECTRICAL CHARACTERISTICS (T<sub>A</sub>=25°C unless otherwise noted)

Parameter	Symbol	Test Condition	Min	Type	Max	Unit
Reverse Voltage	V <sub>BR</sub>	I <sub>R</sub> = 50μA	30			V
Reverse Current	I <sub>R</sub>	V <sub>R</sub> = 10V		0.09	1	μA
		V <sub>R</sub> = 30V		0.13	2	μA
Forward Voltage	V <sub>F</sub>	I <sub>F</sub> = 10mA		0.35	0.39	V
		I <sub>F</sub> = 100mA		0.50	0.65	V
Total Capacitance	C <sub>T</sub>	V <sub>R</sub> =0, f=1MHz		50		pF

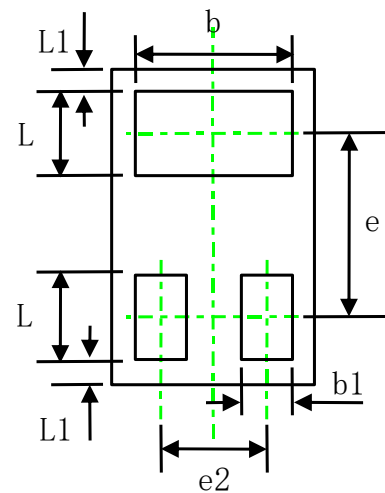
**Typical Electrical and Thermal Characteristics**



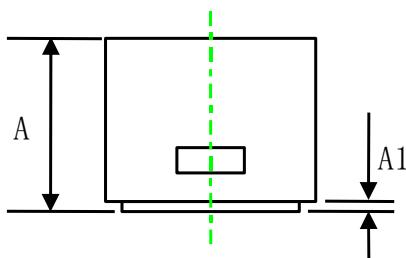
## DFN1006-3L Package Outline Dimensions



TOP VIEW  
[顶视图]



BOTTOM VIEW  
[底视图]



SIDE VIEW  
[侧视图]

Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	0.400	0.550	0.016	0.022
A1	0.000	0.050	0.000	0.002
D	0.950	1.050	0.037	0.041
E	0.550	0.650	0.022	0.026
b	0.400	0.600	0.016	0.024
e	0.65 TYP		0.026 TYP	
e2	0.35 TYP		0.014 TYP	
L1	0.05 REF		0.002 REF	
L	0.200	0.300	0.008	0.012
b1	0.100	0.200	0.004	0.008